

FUJIOKA et al.

Serial No.: 10/098,631

Amendment After Final Rejection dated August 5, 2004

Response to Office Action dated March 11, 2004

Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application. By the present amendment, claim 1 has been amended. Claims 1, 2 and 12-15 are pending in the application.

Listing of Claims:

Claim 1. (*Currently Amended*) A point emission type light emitting element comprising:

a stripe ridge having an n-type layer, an active layer and a p-type layer that are formed from semiconductors on a substrate, so as to emit light from one end face of the stripe ridge,

wherein the stripe ridge has a protruding portion on the end face and the surface of the light emitting element is covered with a shading film except for the tip of the protruding portion, and

wherein ~~a step portion is formed between the stripe ridge and the protruding portion~~ the shading film comprises a material selected from the group comprising Cr/Ni, Cr, Ti/Pt, Ti, Ni, Al, Ag and Au.

Claim 2. (*Previously Presented*) The point emission type light emitting element according to claim 1, wherein said n-type layer, said active layer and said p-type layer comprise nitride semiconductor.

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Claims 3-11. (*Canceled*)

Claim 12. (*Previously Presented*) The point emission type light emitting element according to claim 1, wherein the width of the stripe ridge is in a range from $1\mu\text{m}$ to $100\mu\text{m}$.

Claim 13. (*Previously Presented*) The point emission type light emitting element according to claim 1, wherein the width of the protruding portion is in a range from $1\mu\text{m}$ to $10\mu\text{m}$.

Claim 14. (*Previously Presented*) The point emission type light emitting element according to claim 1, wherein the shading film comprises a material selected from the group consisting of Cr/Ni, TiO_2 , SiO_2 , Cr, Ti/Pt, Ti, Ni, Al, Ag and Au.

Claim 15. (*Previously Presented*) The point emission type light emitting element according to claim 1, wherein the ridge stripe is formed by etching to a depth that does not reach the active layer and the protruding portion is formed by etching to a depth that reaches the n-type layer.